Tohoku University's Invention

Phase-change memory



New material for PRAM with thermal stability

Summary

A phase-change material, which has a high crystallization temperature and is superior in thermal stability of the amorphous phase, which has a composition of the general chemical formula $Ge_{xMyTe100-x-y}$ wherein M indicates one type of element which is selected from the group which comprises Al, Si, Cu, In, and Sn, x is 5.0 to 50.0 (at %) and y is 4.0 to 45.0 (at %) in range, and x and y are selected so that 40 (at %) \leq x+y \leq 60 (at %). This phase-change material further contains, as an additional element L, at least one type of element L which is selected from the group which comprises N, O, Al, Si, P, Cu, In, and Sn in the form of $Ge_{xMyLzTe100-x-y-z}$ wherein z is selected so that 40 (at %) \leq x+y+z \leq 60 (at %).

Effect/Application

Phase-change memory

Patent Data Sheet

8,598,563(US),1333751(KR),201080040813.3(CN),5403565 (JP) (T09-087)

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Characteristics

г					※ 1	 1	 %2	Ж3
	Te (at.%)	Ge (at.%)	(: Al. Si. Cu.) (Zn. In. Sn (at.%)	Additi onal Elem ent	Crystall ization Temper ature	Activati on energy	Melting Temper ature	Electrica resistivi
E	残部	47.5	Al : 5.0	one	222	3.1	690	7×10 ⁶
	//	45.0	Al: 11.0	-	262	3.3	705	7×10 ⁵
章	"	46.0	Al : 6.0	Sn: 1.0	230	3.6	695	5×10°
7	"	44.2	AI: 10.2	In: 0.5	270	3.3	708	6×10 ⁵
_	"	45.2	Si: 10.2	0': 0 5	291	3.5	690	9×10 ³
Ψ	"	44.2	Si : 10.1 Cu : 8.0	0:0.5	298 230	3.7	700	1×10 ³
Ne Ne	"	23.8	Cu: 17.1		202	3.3	570 512	2×106
	"	20.4	Cu: 29.1	-	208	3.4	541	4×10° 2×10³
	11	16.7	Cu: 33.3	-	200	3.4	542	3×10 ²

GeSbTe

ex)Ge:22.2%,Sb22.2%,Te Rest

159 2.3 640 3×10⁴

※ 1 : To keep thermal stability, Large Crystallization Temperature & Activation energy are better

※ 2 : Low is better

※ 3 : 10² is needed for "Read Accuracy"

Contact

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